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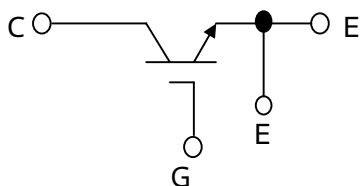
<TENTATIVE SPEC.>

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

- High Input Impedance.
- Enhancement Mode.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTICS		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V_{CES}	4500	V
Gate-Emitter Voltage		V_{GES}	±20	V
Collector Current	RMS (note.1)	$I_{C(rms)}$	1200	A
	Peak Turn-Off (note.2)	I_{CP}	2400	A
Collector Power Dissipation (Tc=25°C)		P_C	5000	W
Junction Temperature		T_j	-40~125	°C
Storage Temperature Range		T_{stg}	-40~125	°C
Mounting Force		-	28~35	kN

note.1

50Hz, half-sine wave

Tf=75°C

without switching losses

note.2

 $V_{cp} < 3600V$ $V_{GE} = \pm 15V, R_G = 7.2 \Omega$ $T_j < 125^\circ C$

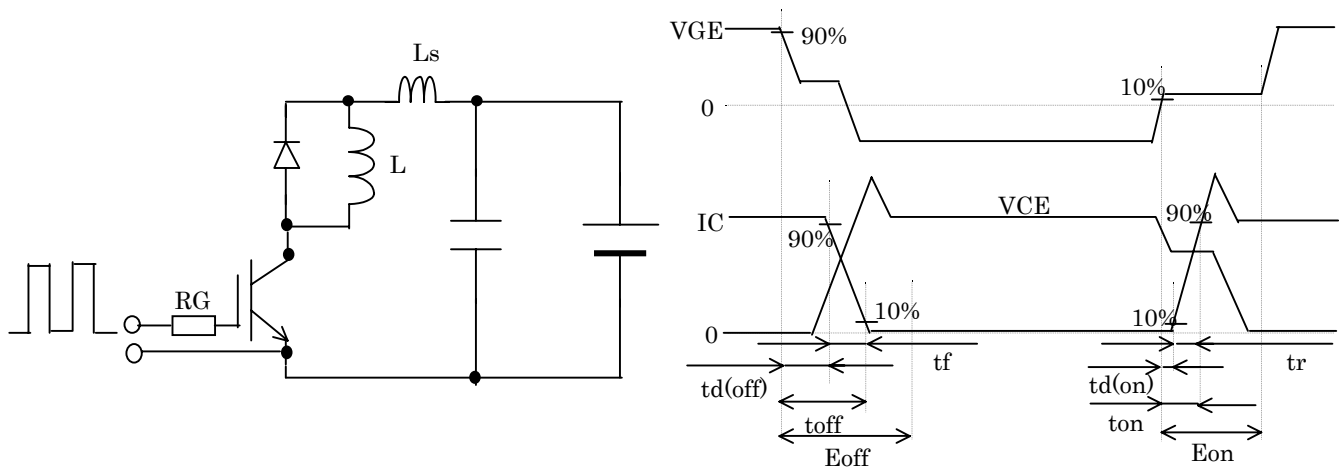
non-repetitive

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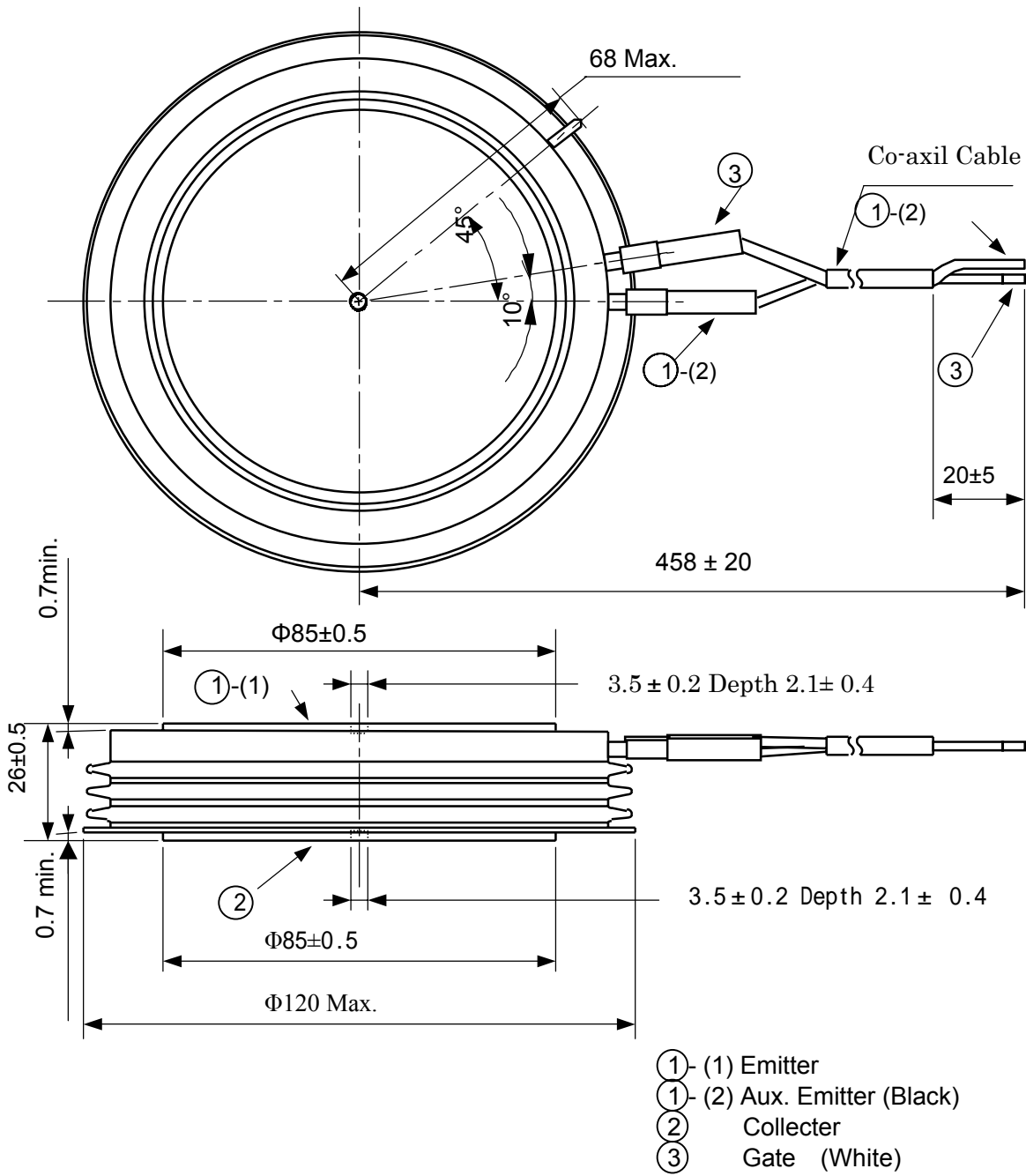
ELECTORICAL CHARACTERISTICS (Tc=125°C : EXCEPT THERMAL RESISTANCE)

CHARACTERISTICS		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE}=\pm 20V, V_{CE}=0V$	-	-	± 50	nA
Collector Cut-off Current		I_{CES}	$V_{CE}=4500V, V_{GE}=0V$	-	-	100	mA
Gate-Emmitter cut-off Voltage		$V_{GE(off)}$	$I_C=1.2A, V_{CE}=5V$	-	5.0	-	V
Collector-Emmitter Saturation Voltage		$V_{CE(sat)}$	$I_C=1200A, V_{CE}=5V$	-	4.0	-	V
Input Capacitance		C_{ies}	$V_{CE}=10V, V_{GE}=0V, f=100kHz$	-	150	-	nF
Switching Time	Rise Time	t_r	$V_{CC}=2700V, I_C=1200A$ $V_{GE}=\pm 15V, L_s=330nH$ $R_{G(on)}/(off)=15/7.2\Omega,$ $di/dt=2500A/us$ (FWD : 1000GXHH25)	-	0.8	-	μs
	Turn-on Time	t_{on}		-	1.5	-	μs
	Fall Time	t_f		-	3.0	-	μs
	Turn-off Time	t_{off}		-	9.0	-	μs
Switching Dissipation	Turn-on Loss	E_{on}	NOTE.3	-	8.5	-	J
	Turn-off Loss	E_{off}		-	5.5	-	J
Short Circuit Capability		SC	$V_{GE}=\pm 15V, t_w=10us$	3000	-	-	V
Thermal Resistance		$R_{th(j-c)}$	Emitter Side	-	-	26	$^{\circ}C/kW$
			Collector Side	-	-	16	$^{\circ}C/kW$
			Double Side	-	-	10	$^{\circ}C/kW$

NOTE.3 : Test circuit and timing chart of switching time



Unit : mm



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